| EMIF02-MIC02F1 |  |
| ---: | ---: |
| IPAD $^{\text {TM }}$ | 2 LINES EMI FILTER |
|  | AND ESD PROTECTION |

## MAIN PRODUCT CHARACTERISTICS:

Where EMI filtering in ESD sensitive equipment is required:

- Mobile phones and communication systems
- Computers, printers and MCU Boards


## DESCRIPTION

The EMIF02-MIC02 is a highly integrated devices designed to suppress EMI/RFI noise in all systems subjected to electromagnetic interferences. The EMIF02 flip chip packaging means the package size is equal to the die size.
This filter includes an ESD protection circuitry which prevents the device from destruction when subjected to ESD surges up 15 kV .

## BENEFITS

- EMI symmetrical (I/O) low-pass filter
- High efficiency in EMI filtering
- Very low PCB space consuming: $1.07 \mathrm{~mm} \times 1.57 \mathrm{~mm}$
- Very thin package: 0.65 mm
- High efficiency in ESD suppression
- High reliability offered by monolithic integration
- High reducing of parasitic elements through integration \& wafer level packaging.

COMPLIES WITH THE FOLLOWING STANDARDS: IEC61000-4-2

| Level 4 | on input pins | 15 kV |
| :--- | :--- | :--- |
|  | 8 kV | (air discharge) <br> (contact discharge) <br> Level 1 on output pins |
|  | 2 kV | (air discharge) |
|  | 2 kV | (contact discharge) |



PIN CONFIGURATION (ball side)


MIL STD 883E - Method 3015-6 Class 3

## BASIC CELL CONFIGURATION



TM : IPAD is a trademark of STMicroelectronics.

EMIF02-MIC02F1
ABSOLUTE RATINGS (limiting values)

| Symbol | Parameter and test conditions | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{T}_{\mathrm{j}}$ | Maximum junction temperature | 125 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {op }}$ | Operating temperature range | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage temperature range | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |

ELECTRICAL CHARACTERISTICS $\left(\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}\right)$

| Symbol | Parameter |
| :---: | :--- |
| $\mathrm{V}_{\mathrm{BR}}$ | Breakdown voltage |
| $\mathrm{I}_{\mathrm{RM}}$ | Leakage current @ $\mathrm{V}_{\mathrm{RM}}$ |
| $\mathrm{V}_{\mathrm{RM}}$ | Stand-off voltage |
| $\mathrm{V}_{\mathrm{CL}}$ | Clamping voltage |
| $\mathrm{R}_{\mathrm{d}}$ | Dynamic impedance |
| $\mathrm{I}_{\mathrm{PP}}$ | Peak pulse current |
| $\mathrm{R}_{\mathrm{I} / \mathrm{O}}$ | Series resistance between Input \& Output |
| $\mathrm{C}_{\text {line }}$ | Input capacitance per line |



| Symbol | Test conditions | Min. | Typ. | Max. | Unit |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{BR}}$ | $\mathrm{I}_{\mathrm{R}}=1 \mathrm{~mA}$ | 14 | 16 |  | V |
| $\mathrm{I}_{\mathrm{RM}}$ | $\mathrm{V}_{\mathrm{RM}}=12 \mathrm{~V}$ per line |  |  | 500 | nA |
| $\mathrm{R}_{\mathrm{I} / \mathrm{O}}$ |  | 423 | 470 | 517 | $\Omega$ |
| $\mathrm{C}_{\text {line }}$ | $@ 0 \mathrm{~V}$ |  | 16 |  | pF |

Fig. 1: $\mathrm{S} 21(\mathrm{~dB})$ attenuation measurement and Aplac simulation.


Fig. 2: Analog crosstalk measurements.


Fig. 3: Digital crosstalk measurement.


Fig. 5: ESD response to IEC61000-4-2 (-15kV air discharge) on one input $V$ (in) and on one output (Vout).


Fig. 4: ESD response to IEC61000-4-2 (+15kV air discharge) on one input V (in) and on one output (Vout).


Fig. 6: Line capacitance versus applied voltage.


Fig. 7: Aplac model.


Fig. 8: Aplac parameters.

| Model D01-ext $B V=7$ <br> CJO = Cz_ext <br> $\mathrm{IBV}=1 \mathrm{u}$ <br> IKF $=1000$ <br> IS = 10f <br> ISR = 100p <br> $\mathrm{N}=1$ <br> $\mathrm{M}=0.3333$ <br> RS = Rs_ext <br> $\mathrm{VJ}=0.6$ <br> $\mathrm{TT}=50 \mathrm{n}$ | Model D01-int $\mathrm{BV}=7$ <br> CJO = Cz_int <br> $\mathrm{IBV}=1 \mathrm{u}$ <br> IKF = 1000 <br> IS = 10f <br> ISR = 100p <br> $\mathrm{N}=1$ <br> $\mathrm{M}=0.3333$ <br> RS = Rs_int <br> $\mathrm{VJ}=0.6$ <br> $\mathrm{TT}=50 \mathrm{n}$ | $\begin{aligned} & \text { Model D01-gnd } \\ & \text { BV }=7 \\ & \text { CJO }=C z \text { _gnd } \\ & \text { IBV }=1 \mathrm{u} \\ & \text { IKF }=1000 \\ & \text { IS }=10 \mathrm{f} \\ & \text { ISR }=100 \mathrm{p} \\ & \mathrm{~N}=1 \\ & \mathrm{M}=0.3333 \\ & \mathrm{RS}=\text { Rs_gnd } \\ & \mathrm{VJ}=0.6 \\ & \mathrm{TT}=50 \mathrm{n} \end{aligned}$ | aplacvar Ls 400pH aplacvar Rs 100 m <br> aplacvar R_470R 482.6 aplacvar Cz_ext 8.73pF aplacvar Rs_ext 850m aplacvar Cz_int 2.9pF aplacvar Rs_int 850 m aplacvar Cz_gnd 215.61pF aplacvar Rs_gnd 470m <br> aplacvar Rgnd 10 m aplacvar Lgnd 48pH aplacvar Cgnd 0.15 pF <br> aplacvar Cox 3.05 pF aplacvar Rsubump 200m |
| :---: | :---: | :---: | :---: |

ORDER CODE


## PACKAGE MECHANICAL DATA <br> FLIP CHIP



## FOOT PRINT RECOMMENDATIONS



## MARKING



## PACKING



OTHER INFORMATION

| Ordering code | Marking | Package | Weight | Base qty | Delivery mode |
| :---: | :---: | :---: | :---: | :---: | :---: |
| EMIF02-MIC02F1 | FJT | Flip Chip | 2.3 mg | 5000 | Tape \& reel (7") |

Note: More packing informations are available in the application note AN1235: "Flip-Chip: Package description and recommandations for use"

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